



Product Summary

V _{(BR)DSS}	R _{DS(on)TYP}	I _D
-20V	6mΩ@-4.5V	-15A
	8.5mΩ@-2.5V	
	15mΩ@-1.8V	

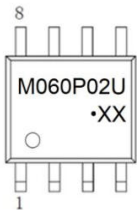
Feature

- Trench Technology Power MOSFET
- Low R_{DS(ON)}
- Low Gate Charge

Application

- Load Switch
- DC/DC Converter

MARKING:

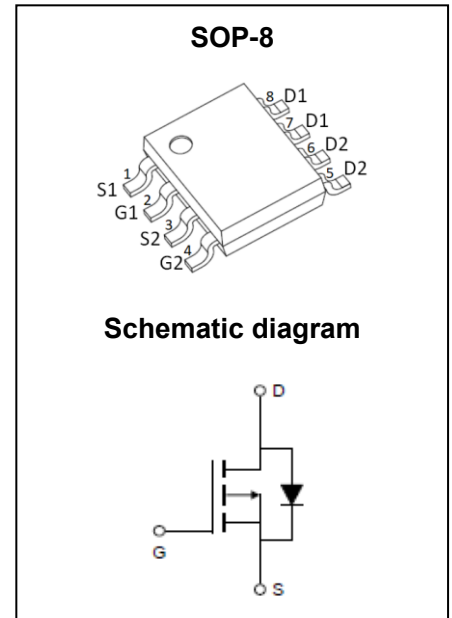


M060P0U2 = Device Code

XX = Date Code

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V _{DS}	-20	V
Gate - Source Voltage	V _{GS}	±12	V
Continuous Drain Current ^{1,5}	I _D	-15	A
	T _A = 25°C		
Pulsed Drain Current ²	I _{DM}	-60	A
Power Dissipation ^{4,5}	P _D	3.3	W
	T _A = 25°C		
Thermal Resistance from Junction to Ambient ⁵	R _{θJA}	38	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C



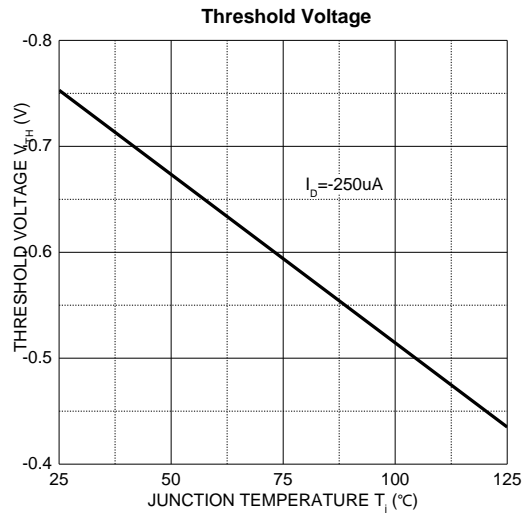
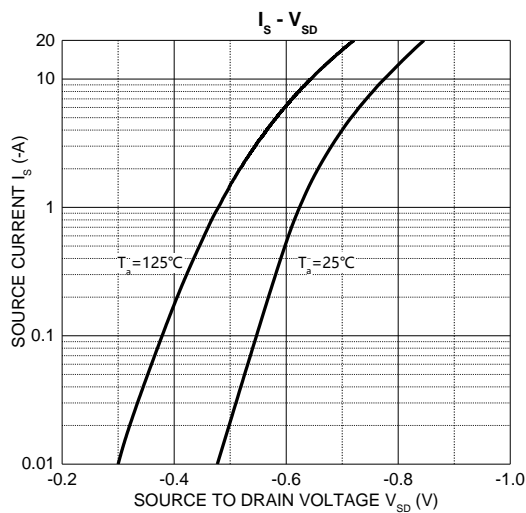
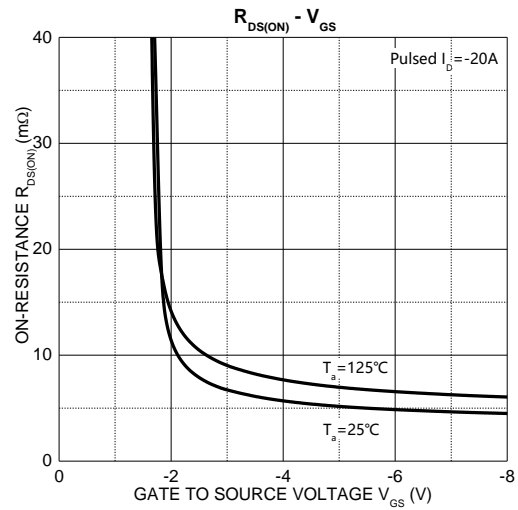
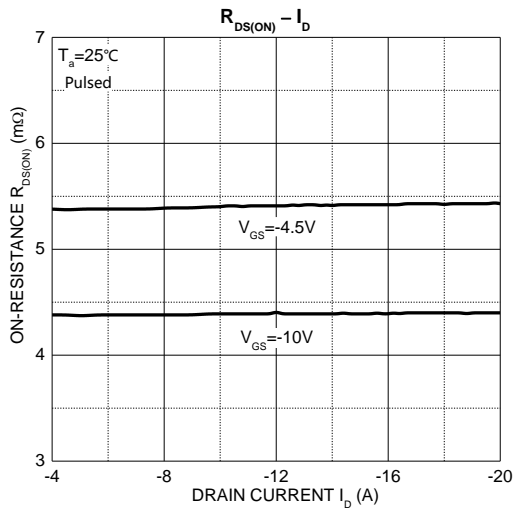
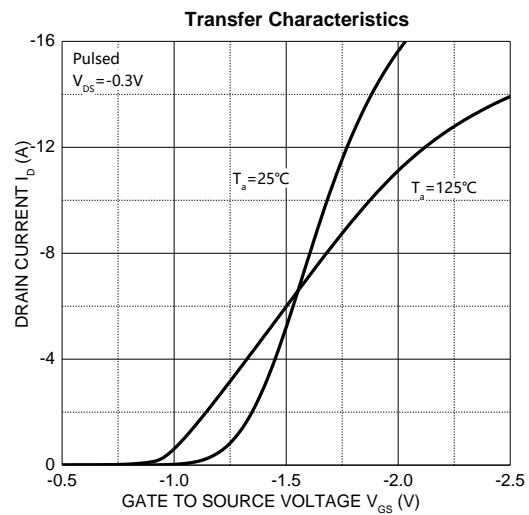
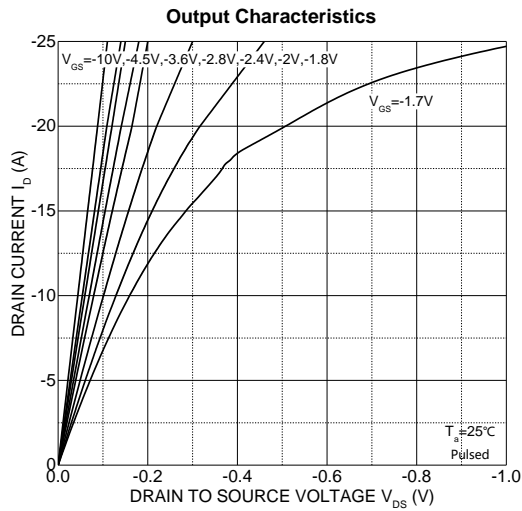
MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 8V, V_{DS} = 0V$			± 100	nA
On Characteristics³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.7	-1.0	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -14A$		6	8	m Ω
		$V_{GS} = -2.5V, I_D = -12A$		8.5	11	
		$V_{GS} = -1.8V, I_D = -11A$		15	23	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		4027		pF
Output Capacitance	C_{oss}			961		
Reverse Transfer Capacitance	C_{rss}			962		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		4.5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = -10V, V_{GS} = -10V, I_D = -14A$		66		nC
Gate-source Charge	Q_{gs}			10.2		
Gate-drain Charge	Q_{gd}			29.7		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -10V, V_{GS} = -10V, I_D = -15A, R_G = 2.7\Omega$		7		ns
Turn-on Rise Time	t_r			57		
Turn-off Delay Time	$t_{d(off)}$			110		
Turn-off Fall Time	t_f			40		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = -10A$			-1.2	V

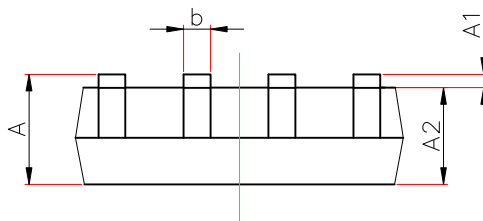
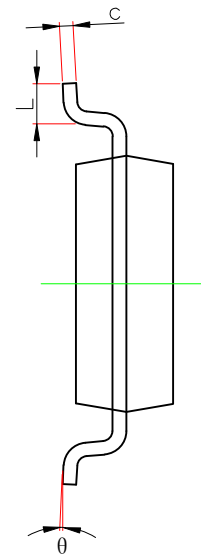
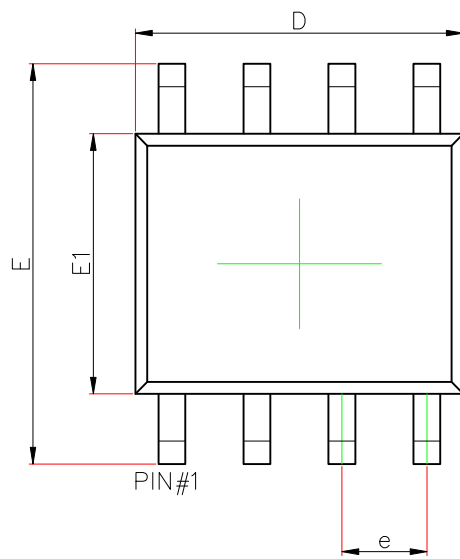
Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 5.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



SOP8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.156	0.250	0.006	0.010
D	4.700	5.100	0.185	0.201
e	1.270(BSC)		0.050(BSC)	
E	5.800	6.200	0.228	0.244
E1	3.700	4.100	0.146	0.161
L	0.400	1.270	0.016	0.05
θ	0°	8°	0°	8°

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.